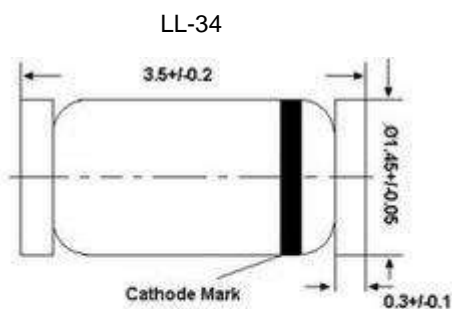


Silicon Epitaxial Planar Zener Diodes

In MiniMELF case especially for automatic insertion.

These diodes are also available in DO-35 case with the type designation BZX55B...



Glass case MiniMELF
 Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^\circ\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	$R_{\theta\text{JA}}$	0.3 ¹⁾	K/mW
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1	V

¹⁾ Valid provided that electrodes are kept at ambient temperature

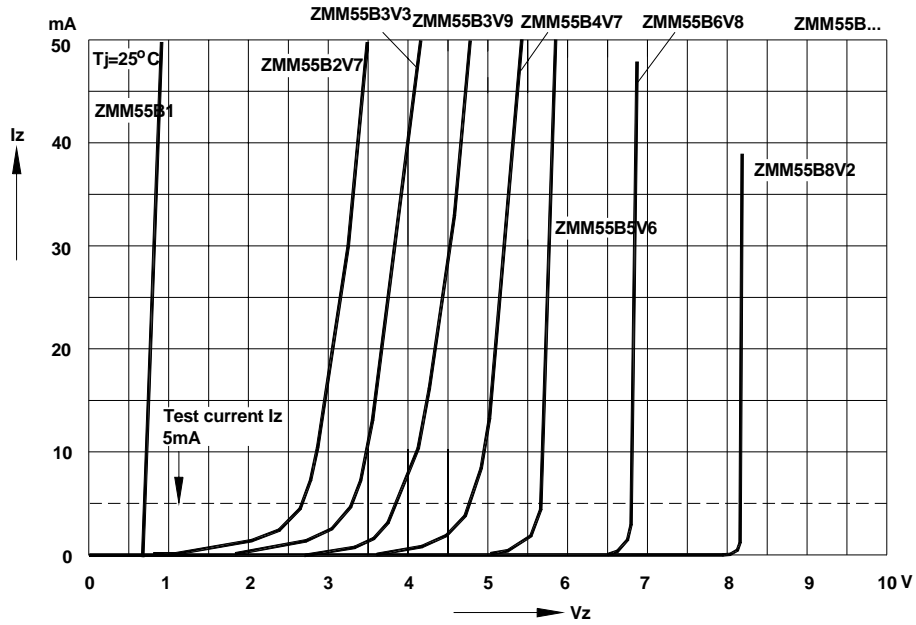
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Type ZMM55B	Zener Voltage Range ¹⁾			Dynamic Resistance			Reverse Leakage Current			Temp coefficient of Zener Voltage TKvz (%/K)
	V_{Znom}	V_{ZT}	at I_{ZT}	Z_{ZT}	Z_{ZK}	at I_{ZK}	$T_a = 25\text{ }^\circ\text{C}$	$T_a = 125\text{ }^\circ\text{C}$	at V_R	
	(V)	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (μA)	Max. (μA)	(V)	
1 ²⁾	0.75	0.73...0.77	5	8	50	1	-	-	-	-0.26...-0.23
2V0	2	1.96...2.04	5	85	600	1	100	200	1	-0.09...-0.06
2V2	2.2	2.16...2.24	5	85	600	1	75	160	1	-0.09...-0.06
2V4	2.4	2.35...2.45	5	85	600	1	50	100	1	-0.09...-0.06
2V7	2.7	2.65...2.75	5	85	600	1	10	50	1	-0.09...-0.06
3V0	3	2.94...3.06	5	85	600	1	4	40	1	-0.08...-0.05
3V3	3.3	3.23...3.37	5	85	600	1	2	40	1	-0.08...-0.05
3V6	3.6	3.53...3.67	5	85	600	1	2	40	1	-0.08...-0.05
3V9	3.9	3.82...3.98	5	85	600	1	2	40	1	-0.08...-0.05
4V3	4.3	4.21...4.39	5	75	600	1	1	20	1	-0.06...-0.03
4V7	4.7	4.61...4.79	5	60	600	1	0.5	10	1	-0.05...+0.02
5V1	5.1	5...5.2	5	35	550	1	0.1	2	1	-0.02...+0.02
5V6	5.6	5.49...5.71	5	25	450	1	0.1	2	1	-0.05...+0.05
6V2	6.2	6.08...6.32	5	10	200	1	0.1	2	2	0.03...0.06
6V8	6.8	6.66...6.94	5	8	150	1	0.1	2	3	0.03...0.07
7V5	7.5	7.35...7.65	5	7	50	1	0.1	2	5	0.03...0.07
8V2	8.2	8.04...8.36	5	7	50	1	0.1	2	6.2	0.03...0.08
9V1	9.1	8.92...9.28	5	10	50	1	0.1	2	6.8	0.03...0.09
10	10	9.8...10.2	5	15	70	1	0.1	2	7.5	0.03...0.1
11	11	10.78...11.22	5	20	70	1	0.1	2	8.2	0.03...0.11
12	12	11.76...12.24	5	20	90	1	0.1	2	9.1	0.03...0.11
13	13	12.74...13.26	5	26	110	1	0.1	2	10	0.03...0.11
15	15	14.7...15.3	5	30	110	1	0.1	2	11	0.03...0.11
16	16	15.68...16.32	5	40	170	1	0.1	2	12	0.03...0.11
18	18	17.64...18.36	5	50	170	1	0.1	2	13	0.03...0.11
20	20	19.6...20.4	5	55	220	1	0.1	2	15	0.03...0.11
22	22	21.56...22.44	5	55	220	1	0.1	2	16	0.04...0.12
24	24	23.52...24.48	5	80	220	1	0.1	2	18	0.04...0.12
27	27	26.46...27.54	5	80	220	1	0.1	2	20	0.04...0.12
30	30	29.4...30.6	5	80	220	1	0.1	2	22	0.04...0.12
33	33	32.34...33.66	5	80	220	1	0.1	2	24	0.04...0.12
36	36	35.28...36.72	5	80	220	1	0.1	2	27	0.04...0.12
39	39	38.22...39.78	2.5	90	500	0.5	0.1	5	30	0.04...0.12
43	43	42.14...43.86	2.5	90	500	0.5	0.1	5	33	0.04...0.12
47	47	46.06...47.94	2.5	110	600	0.5	0.1	5	36	0.04...0.12
51	51	49.98...52.02	2.5	125	700	0.5	0.1	10	39	0.04...0.12
56	56	54.88...57.12	2.5	135	700	0.5	0.1	10	43	0.04...0.12
62	62	60.76...63.24	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
68	68	66.64...69.36	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
75	75	73.5...76.5	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

¹⁾ Tested with pulses $t_p = 20\text{ ms}$.

²⁾ The ZMM55B1 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode electrode to the negative pole.

Breakdown characteristics
 $T_j = \text{constant (pulsed)}$



Breakdown characteristics
 $T_j = \text{constant (pulsed)}$

